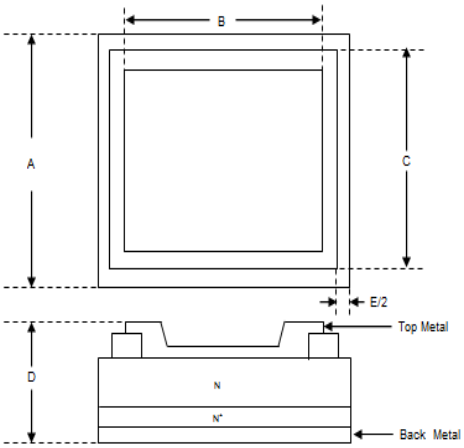
TSB75T060S(A)S-255A

5A/60V, low VF Schottky barrier diode with trench MOS structure

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	1905 μm	75 mil
	Top Metal Pad Size (B)	1812μm	71mil
	Chip Size (C)	1825μm	72mil
	Wafer Thickness (D)	255 μm	9.5 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	TSB75T060SS-255A	Al/Ag
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23 ±3)	

Electrical Characteristics (T_J=25)(1)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V_{BR}	Reverse Breakdown Voltage	62	70	-	V	I_R =100μA
V_F	Instantaneous Forward Voltage	-	0.485	0.520	V	I_F =5A(2)
I_R	Reverse Leakage Current	-	5	40		V_R =65V
T_J, T_{STG}	Operating and Storage Temperature	-40 to 150 Max				

Note:

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assumes the dies are assembled in DO-27 packages(Al Wire 15milX2). Actual performance may degrade when assembled. YJ does not guarantee device performance after assembly;

(3) ;